

SCH1430

Power MOSFET 20V, 125mΩ, 2A, Single N-Channel

This low-profile high-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

Features

- Low On-Resistance
- 1.8V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mm)

Typical Applications

- Load Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	20	V
Gate to Source Voltage	V _{GSS}	±12	V
Drain Current (DC)	I _D	2	A
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%	I _{DP}	8	A
Power Dissipation When mounted on ceramic substrate (900mm ² × 0.8mm)	P _D	0.8	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² × 0.8mm)	R _{θJA}	156.2	°C/W

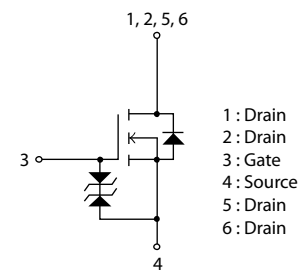


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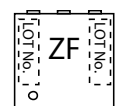
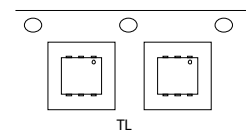
V _{DSS}	R _{DS(on)} Max	I _D Max
20V	125mΩ@ 4.5V	2A
	190mΩ@ 2.5V	
	310mΩ@ 1.8V	

ELECTRICAL CONNECTION N-Channel



PACKING TYPE : TL

MARKING



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

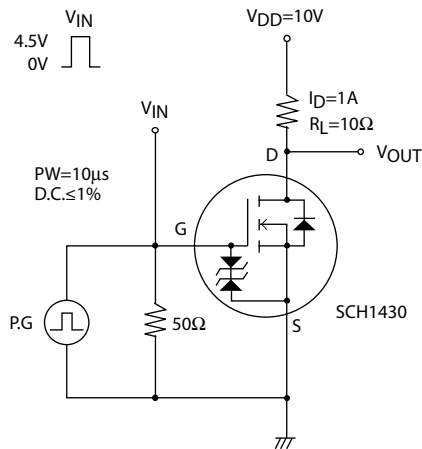
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ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

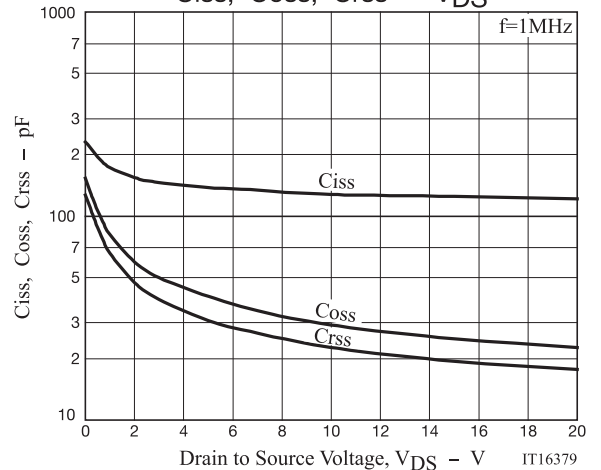
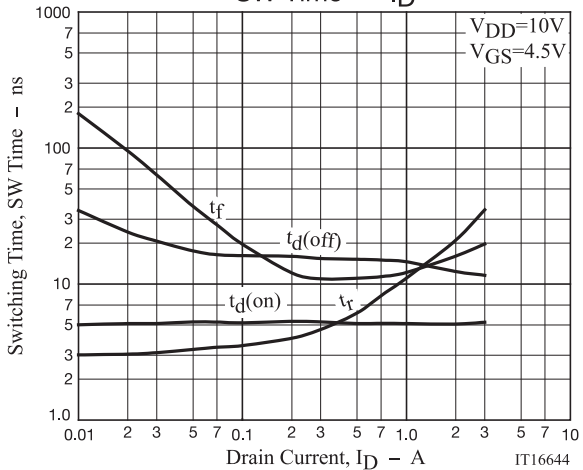
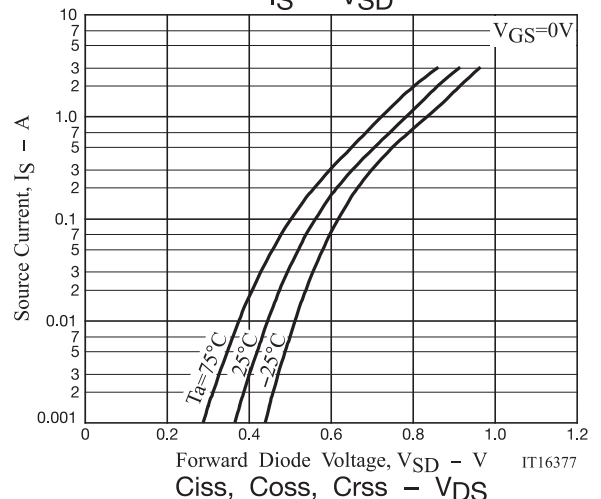
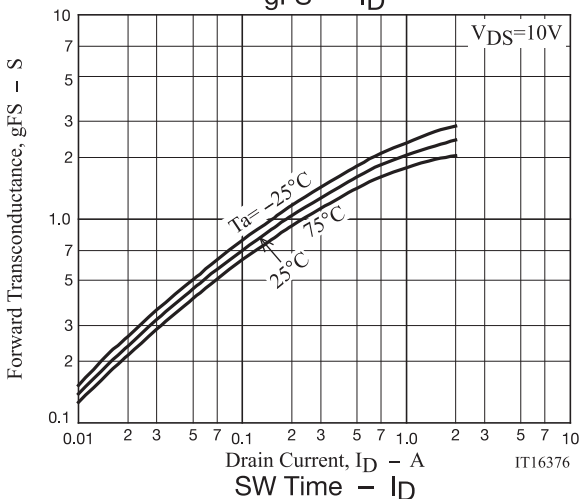
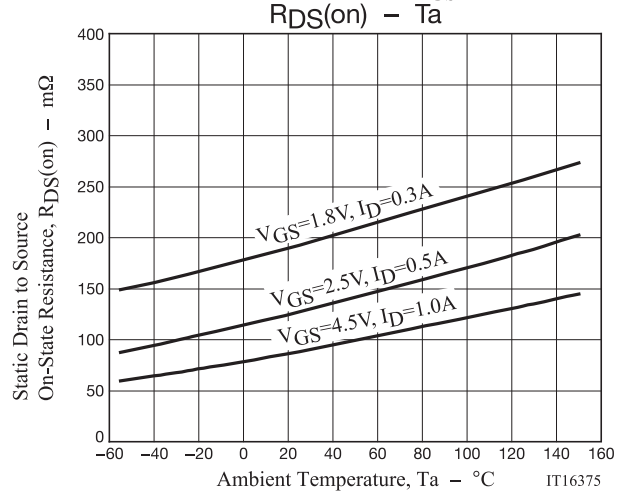
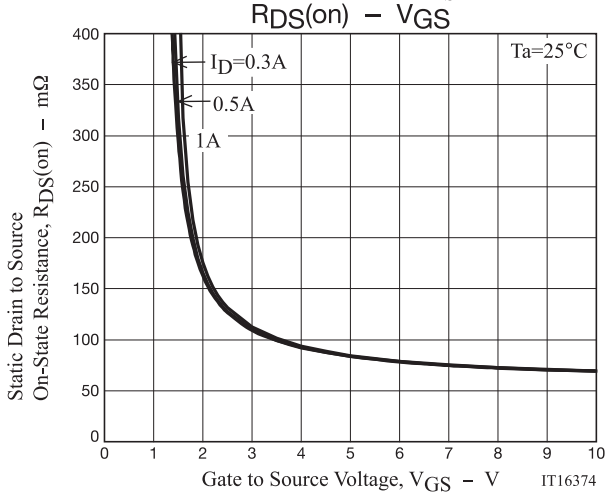
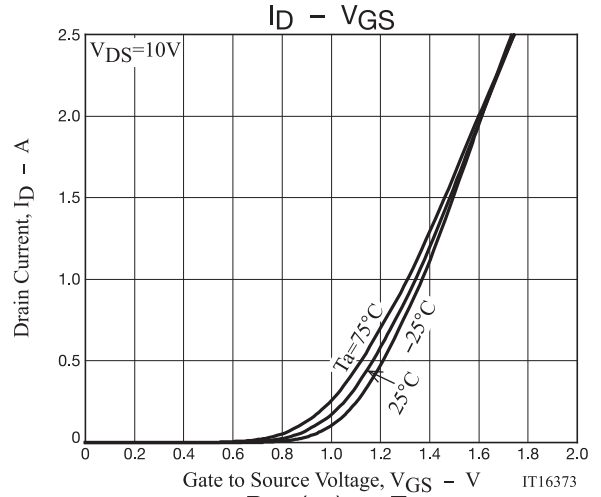
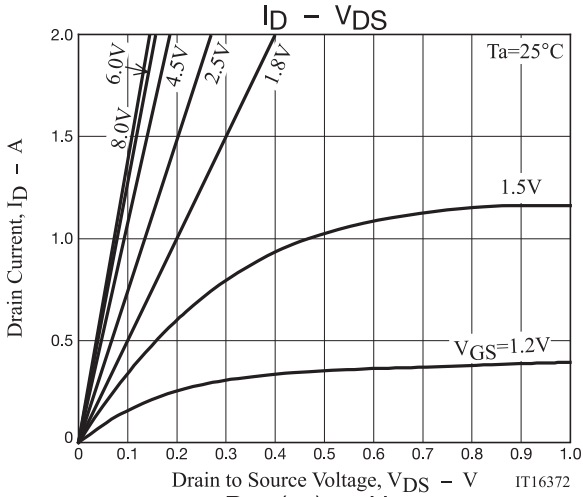
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=20V, VGS=0V			1	μA
Gate to Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Gate Threshold Voltage	VGS(th)	VDS=10V, ID=1mA	0.4		1.3	V
Forward Transconductance	gFS	VDS=10V, ID=1A		1.9		S
Static Drain to Source On-State Resistance	RDS(on)1	ID=1A, VGS=4.5V		93	125	mΩ
	RDS(on)2	ID=0.5A, VGS=2.5V		135	190	mΩ
	RDS(on)3	ID=0.3A, VGS=1.8V		200	310	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		128		pF
Output Capacitance	Coss			28		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit		5.1		ns
Rise Time	t _r			11		ns
Turn-OFF Delay Time	t _{d(off)}			14.5		ns
Fall Time	t _f			12		ns
Total Gate Charge	Qg				1.8	
Gate to Source Charge	Qgs	VDS=10V, VGS=4.5V, ID=2A		0.3		nC
Gate to Drain "Miller" Charge	Qgd			0.55		nC
Forward Diode Voltage	VSD	IS=2A, VGS=0V		0.85	1.2	V

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

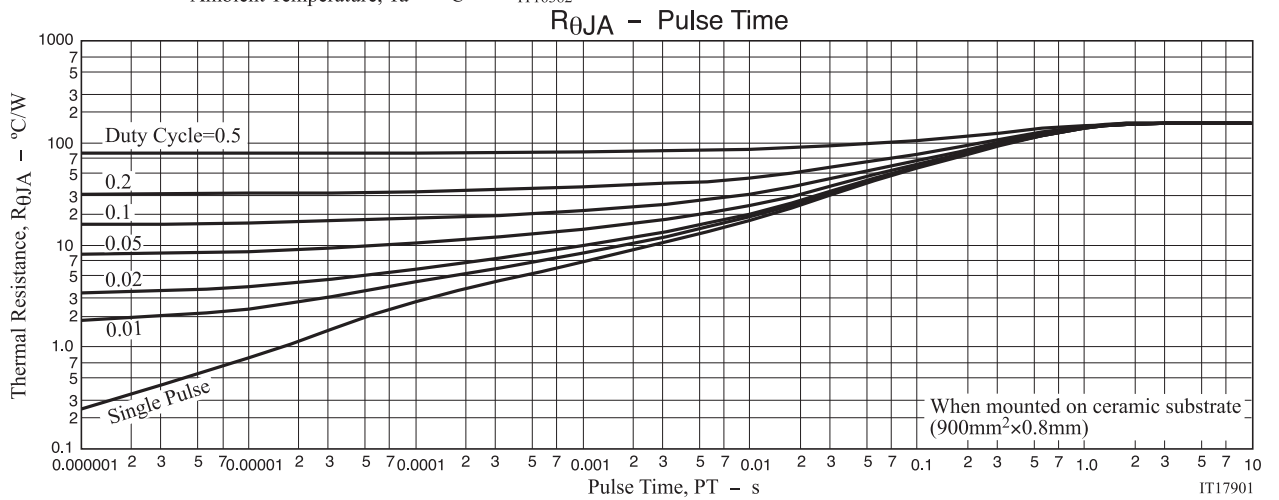
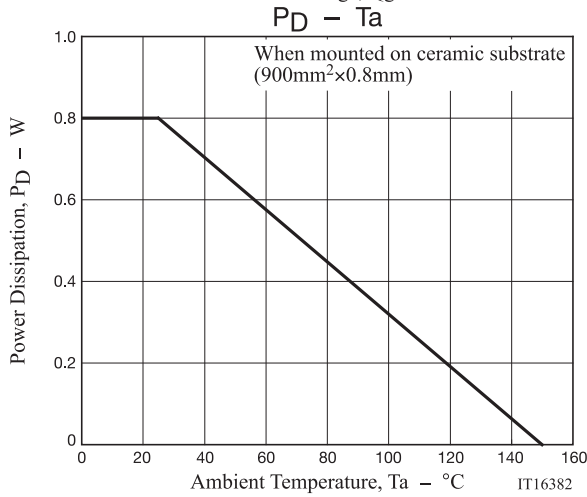
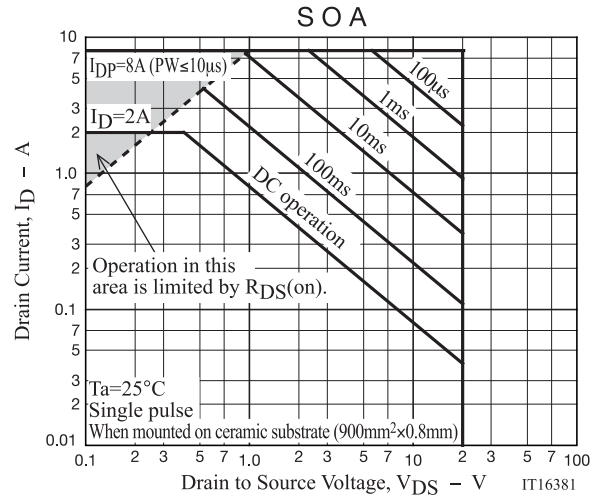
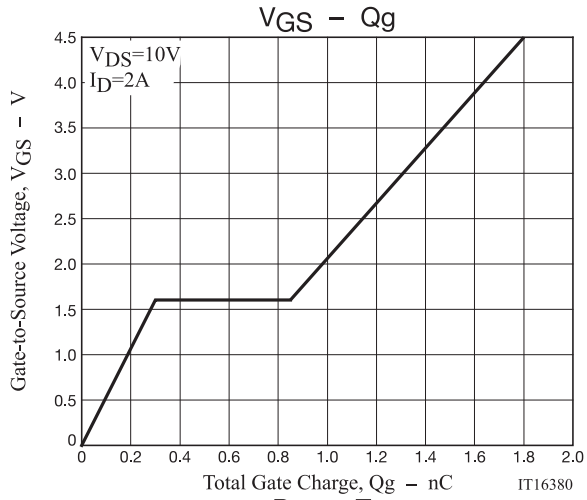
Switching Time Test Circuit



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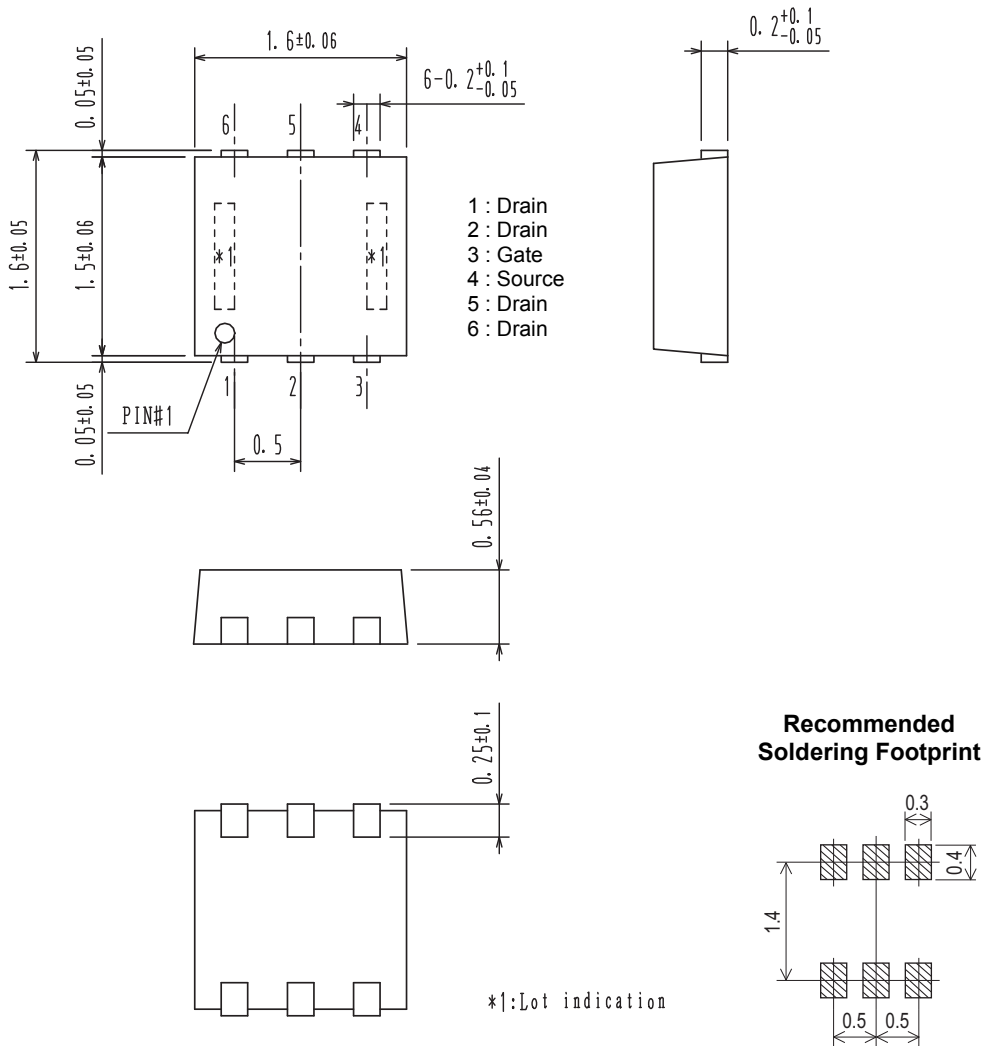


SCH1430

PACKAGE DIMENSIONS

unit : mm

SOT-563 / SCH6
CASE 463AB
ISSUE O



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
SCH1430-TL-H	ZF	SOT-563 / SCH6 (Pb-Free / Halogen Free)	5,000 / Tape & Reel
SCH1430-TL-W			

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the SCH1430 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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